

RGB



# SANYO SEMICONDUCTOR

2SD386, 386A  
2SD387, 387A

(2SD386, 386A) — NPN Triple Diffused Planar Type Silicon Transistor  
(2SD387, 387A) — For Vertical Deflection Output of Television

Absolute Maximum Ratings at Ta=25°C

	2SD386	2SD386A	2SD387	2SD387A	
Collector to Base Voltage, V <sub>CB0</sub>	200	200	200	200	V
Collector to Emitter Voltage, V <sub>CEO</sub>	120	150	120	150	V
Emitter to Base Voltage, V <sub>EB0</sub>	6	6	6	6	V
Collector Current, I <sub>C</sub>	3	2	3	2	A
Peak Collector Current, i <sub>CP</sub>	10	10	10	10	A
Collector Dissipation, P <sub>C</sub>					
	T <sub>c</sub> =25°C	25	25	25	W
	T <sub>a</sub> =25°C	1.75	1.75	1.75	W
Junction Temperature, T <sub>j</sub>	150	150	150	150	°C
Storage Temperature, T <sub>stg</sub>	→	→	→	-40→+150	°C

Electrical Characteristics at Ta=25°C

		min	typ	max	unit
Collector Cutoff Current, I <sub>CB0</sub>	V <sub>CB</sub> =180V, I <sub>E</sub> =0			1.0	mA
Emitter Cutoff Current, I <sub>EB0</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			5	mA
DC Current Gain, h <sub>FE</sub> *	V <sub>CE</sub> =2V, I <sub>C</sub> =0.5A	40*		320*	
Gain Bandwidth Product, f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =0.5A		8		MHz
C-E Saturation Voltage, V <sub>CE(sat)</sub>	I <sub>C</sub> =1A, I <sub>B</sub> =0.1A	2SD386, 387		1.0	V
		2SD386A, 387A		1.5	V
B-E Saturation Voltage, V <sub>BE(sat)</sub>	I <sub>C</sub> =1A, I <sub>B</sub> =0.1A			1.8	V

\*2SD386, 386A, 387, 387A are classified as follows:

C:	40	80
D:	60	120
E:	100	200
F:	160	320

Case Outline (unit:mm)



